













#### OPA180, OPA2180, OPA4180

SBOS584D - NOVEMBER 2011 - REVISED MAY 2014

# OPAx180 0.1-μV/°C Drift, Low-Noise, Rail-to-Rail Output, 36-V, **Zero-Drift Operational Amplifiers**

#### **Features**

Low Offset Voltage: 75 µV (max)

Zero-Drift: 0.1 µV/°C Low Noise: 10 nV/√Hz Very Low 1 / f Noise **Excellent DC Precision:** 

> PSRR: 126 dB CMRR: 114 dB

 Open-Loop Gain (A<sub>OI</sub>): 120 dB Quiescent Current: 525 µA (max) Wide Supply Range: ±2 V to ±18 V

Rail-to-Rail Output: Input Includes Negative Rail Low Bias Current: 250 pA (typ)

**RFI Filtered Inputs** MicroSIZE Packages

## **Applications**

- **Bridge Amplifiers**
- Strain Gauges
- **Test Equipment**
- **Transducer Applications**
- **Temperature Measurement**
- Electronic Scales
- Medical Instrumentation
- **Resister Thermal Detectors**
- **Precision Active Filters**

## 3 Description

The OPA180, OPA2180, and OPA4180 operational amplifiers use zero-drift techniques to simultaneously provide low offset voltage (75 µV), and near zero-drift over time and temperature. These miniature, highprecision, low quiescent current amplifiers offer high input impedance and rail-to-rail output swing within 18 mV of the rails. The input common-mode range includes the negative rail. Either single or dual supplies can be used in the range of 4.0 V to 36 V (±2 V to ±18 V).

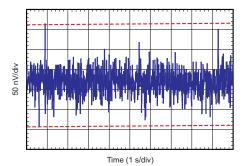
The dual version is offered in VSSOP-8 and SOIC-8 packages. The quad is offered in SOIC-14 and TSSOP-14 packages. All versions are specified for operation from -40°C to 105°C.

#### Device Information<sup>(1)</sup>

DEVICE NAME	PACKAGE	BODY SIZE (NOM)	
	SOT23 (5)	1.60 mm × 2.90 mm	
OPA180	VSSOP, MSOP (8)	3.00 mm × 3.00 mm	
	SOIC (8)	4.90 mm × 3.91 mm	
OPA2180	VSSOP, MSOP (8)	3.00 mm × 3.00 mm	
OPA2160	SOIC (8)	4.90 mm × 3.91 mm	
ODA 44.00	TSSOP (14)	5.00 mm × 4.40 mm	
OPA4180	SOIC (14)	8.65 mm × 3.91 mm	

(1) For all available packages, see the orderable addendum at the end of the datasheet.





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## 4 Revision History

Changes from Revision C (December 2012) to Revision D

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

•	Changed format to meet latest data sheet standards; added Device Functional Modes, Application and Implementation, and Power Supply Recommendations sections, and moved existing sections	1
•	Added OPA180 to document	1
•	Added Device Information table	1
•	Deleted Package Information table	3
•	OPA180 pin out drawings	3
•	Added Pin Functions table	4
•	Added Recommended Operating Conditions table	
•	Added Thermal Information: OPA180 table	5
•	Changed Offset Voltage, Long-term stability parameter typical specification in Electrical Characteristics table	6
•	Changed last sentence of EMI Rejection section	14
Cł	hanges from Revision B (December 2011) to Revision C	Page
•	Changed product status from Mixed Status to Production Data	1
•	Changed OPA4180 status to Production Data	1
•	Added package marking to OPS2180 VSSOP-8 row in Package Information table	3
•	Deleted ordering number and transport media columns from Package Information table	3
•	Changed Input Bias Current section in Electrical Characteristics (V <sub>S</sub> = +4 V to +36 V) table	6
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Changes from Revision A (November 2011) to Revision B

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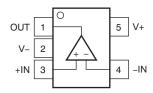


## 5 Zero-Drift Amplifier Portfolio

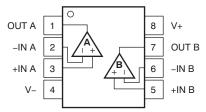
VERSION	PRODUCT	OFFSET VOLTAGE (μV)	OFFSET VOLTAGE DRIFT (μV/°C)	BANDWIDTH (MHz)
	OPA188 (4 V to 36 V)	25	0.085	2
	OPA180 (4 V to 36 V)	75	0.35	2
Single	OPA333 (5 V)	10	0.05	0.35
	OPA378 (5 V)	50	0.25	0.9
	OPA735 (12 V)	UCT         (μV)         (μV°C)           V to 36 V)         25         0.085           V to 36 V)         75         0.35           3 (5 V)         10         0.05           3 (5 V)         50         0.25           (12 V)         5         0.05           V to 36 V)         25         0.085           V to 36 V)         75         0.35           3 (5 V)         10         0.05           8 (5 V)         50         0.25           5 (12 V)         5         0.05           V to 36 V)         25         0.085           V to 36 V)         75         0.35	0.05	1.6
	OPA2188 (4 V to 36 V)	25	0.085	2
	OPA2180 (4 V to 36 V)	75	0.35	2
Dual	OPA2333 (5 V)	10	0.05	0.35
	OPA2378 (5 V)	50	0.25	0.9
	OPA2735 (12 V)	5	(μV/°C)  0.085  0.35  0.05  0.25  0.085  0.35  0.085  0.35  0.05  0.05  0.25  0.35  0.35  0.35	1.6
	OPA4188 (4 V to 36 V)	25	0.085	2
Quad	OPA4180 (4 V to 36 V)	75	0.35	2
	OPA4330 (5 V)	50	0.25	0.35

## 6 Pin Configuration and Functions

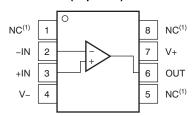
OPA180 DBV Package (SOT23-5) (Top View)



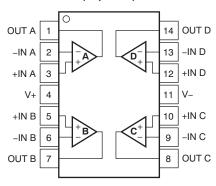
OPA2180 D, DGK Packages (SOIC-8, VSSOP-8) (Top View)



OPA180 D and DGK Packages (SO-8 and MSOP-8) (Top View)



OPA4180 D, PW Packages (SOIC-14, TSSOP-14) (Top View)





#### **Pin Functions**

		PIN					
	OPA	OPA180 OPA21		OPA4180	DESCRIPTION		
NAME	DBV	D (8), DGK	D (8), DGK	D (14), PW	- DESCRIPTION		
–IN A	4	2	2	2	Inverting input		
+IN A	3	3	3	3	Noninverting input		
–IN B	_	_	6	6	Inverting input		
+IN B	_	_	5	5	Noninverting input		
-IN C	_	_	_	9	Inverting input		
+IN C	_	_	_	10	Noninverting input		
–IN D	_	_	_	13	Inverting input		
+IN D	_	_	_	12	Noninverting input		
OUT A	1	6	1	1	Output		
OUT B	_	_	7	7	Output		
OUT C	_	_	_	8	Output		
OUT D	_	_	_	14	Output		
V-	2	4	4	11	Negative supply or ground (for single-supply operation)		
V+	5	7	8	4	Positive supply or ground (for single-supply operation)		

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	nee-an temperature range (unless our	,		
		MIN	MAX	UNIT
Supply voltage			±20, 40 (single supply)	V
Signal input	Voltage	(V-) - 0.5	(V+) + 0.5	V
terminals	Current		±10	mA
Output short-cir	cuit (2)		Continuous	
Operating temp	erature	-55	105	°C
Storage temper	ature	-65	150	°C
Junction temper	rature		150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 7.2 Handling Ratings

			MIN	MAX	UNIT
T <sub>stg</sub>	Storage temperature range	ge	-65	150	°C
.,		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	-1.5	1.5	1.37
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	-1	1	kV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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<sup>(2)</sup> Short-circuit to ground, one amplifier per package.



## 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage [()/1) ()/ )]	Single supply	4.5		36	V
Supply voltage [(V+) – (V–)]	Bipolar supply	±2.25		±18	V
Operating temperature		-40		105	°C

#### 7.4 Thermal Information: OPA180

7					
			OPA180		
	THERMAL METRIC <sup>(1)</sup>	D (SO)	DBV (SOT23)	DGK (MSOP)	UNIT
		8 PINS	5 PINS	8 PINS	-
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.8	158.8	180.4	
R <sub>0JC(top)</sub>	Junction-to-case(top) thermal resistance	60.1	60.7	67.9	
$R_{\theta JB}$	Junction-to-board thermal resistance	56.4	44.8	102.1	°C/W
ΨЈТ	Junction-to-top characterization parameter	12.8	1.6	10.4	*C/VV
$\Psi_{JB}$	Junction-to-board characterization parameter	55.9	4.2	100.3	
R <sub>0JC(bot)</sub>	Junction-to-case(bottom) thermal resistance	N/A	N/A	N/A	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

#### 7.5 Thermal Information: OPA2180

		OP	A2180	
	THERMAL METRIC <sup>(1)</sup>	D (SO)	DGK (MSOP)	UNIT
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	111.0	159.3	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	54.9	37.4	
$R_{\theta JB}$	Junction-to-board thermal resistance	51.7	48.5	90.444
ΨЈТ	Junction-to-top characterization parameter	9.3	1.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	51.1	77.1	
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	n/a	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

#### 7.6 Thermal Information: OPA4180

		OP.	OPA4180		
	Junction-to-ambient thermal resistance  Junction-to-case (top) thermal resistance  Junction-to-board thermal resistance  Junction-to-top characterization parameter  Junction-to-board characterization parameter  Junction-to-case (bottom) thermal resistance	D (SO)	PW (TSSOP)	UNIT	
		14 PINS	14 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	93.2	106.9		
R <sub>0</sub> JC(top)	Junction-to-case (top) thermal resistance	51.8	24.4		
R <sub>0JB</sub>	Junction-to-board thermal resistance	49.4	59.3	90.444	
ΨЈТ	Junction-to-top characterization parameter	13.5	0.6	°C/W	
ΨЈВ	Junction-to-board characterization parameter	42.2	54.3		
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	n/a	n/a		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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# 7.7 Electrical Characteristics: $V_S = \pm 2 \text{ V to } \pm 18 \text{ V (V}_S = 4 \text{ V to } 36 \text{ V)}$

At  $T_A = 25$ °C,  $R_L = 10 \text{ k}\Omega$  connected to  $V_S / 2$ , and  $V_{COM} = V_{OUT} = V_S / 2$ , unless otherwise noted.

	PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET \	VOLTAGE						
V <sub>IO</sub>	Input offset voltage				15	75	μV
dV <sub>IO</sub> /dT	Input offset voltage drift		$T_A = -40$ °C to 105°C		0.1	0.35	μV/°C
			$V_S = 4 \text{ V to } 36 \text{ V}, V_{CM} = V_S / 2$		0.1	0.5	μV/V
PSRR	Power-supply rejection ra	tio	$T_A = -40$ °C to 105°C, $V_S = 4$ V to 36 V, $V_{CM} = V_S / 2$			0.5	μV/V
	Long-term stability				4 <sup>(1)</sup>		μV
	Channel separation, dc				1		μV/V
INPUT BI	AS CURRENT						
			OPA2180		±0.25	±1	nA
	1		OPA2180, $T_A = -40^{\circ}\text{C}$ to $105^{\circ}\text{C}$			±5	nA
NPUT BIAS  ID  NOISE  NPUT VOL  VCM  CMRR  NPUT IMPE  Lid  Zic  DPEN-LOO  AoL  FREQUENC  GBW	Input bias current		OPA4180, OPA180		±0.25	±1.7	nA
			OPA4180, OPA180, T <sub>A</sub> = -40°C to 105°C		15 75 0.1 0.38 0.1 0.5 4(1) 1  ±0.25 ±1 ±0.25 ±1.7  ±0.25 ±1.7  10  10  (V+) -1.5  114  104  100    6 6    9.5	±6	nA
			OPA2180		±0.5	±2	nA
			OPA2180, T <sub>A</sub> = -40°C to 105°C			±2.5	nA
I <sub>IO</sub>	Input offset current		OPA4180, OPA180			±3.4	nA
			OPA4180, OPA180, T <sub>A</sub> = -40°C to 105°C			75 0.35 0.5 0.5  ±1 ±5 ±1.7 ±6 ±2 ±2.5	nA
NOISE							
	Input voltage noise		f = 0.1 Hz to 10 Hz		0.25		$\mu V_{PP}$
e <sub>n</sub>	Input voltage noise densit	у	f = 1 kHz		10		nV/√ <del>Hz</del>
in	Input current noise densit	у	f = 1 kHz		10		fA/√ <del>Hz</del>
INPUT VC	LTAGE RANGE						
V <sub>CM</sub>	Common-mode voltage ra	ange		V-		(V+) - 1.5	V
-	•	-	$(V-) < V_{CM} < (V+) - 1.5 V$	104	114		dB
CMRR	Common-mode rejection	ratio	T <sub>A</sub> = -40°C to 105°C, (V-) + 0.5 V < V <sub>CM</sub> < (V+) - 1.5 V	100	104		dB
INPUT IM	PEDANCE						
z <sub>id</sub>	Differential				100    6		$M\Omega \parallel pF$
z <sub>ic</sub>	Common-mode				6    9.5		10 <sup>12</sup> Ω    pF
OPEN-LO	OP GAIN						
			$(V-) + 500 \text{ mV} < V_O < (V+) - 500 \text{ mV}, R_L = 10 \text{ k}\Omega$	110	120		dB
A <sub>OL</sub>	Open-loop voltage gain		$T_A = -40$ °C to 105°C, (V-) + 500 mV < V <sub>O</sub> < (V+) - 500 mV, R <sub>L</sub> = 10 kΩ	104	114		dB
FREQUE	NCY RESPONSE						
GBW	Gain bandwidth product				2		MHz
SR	Slew rate		G = 1		0.8	·	V/µs
	0-441	0.1%	V <sub>S</sub> = ±18 V, G = 1, 10-V step		22		μs
t <sub>s</sub>	Settling time	0.01%	V <sub>S</sub> = ±18 V, G = 1, 10-V step		30		μs
t <sub>or</sub>	Overload recovery time		$V_{IN} \times G = V_{S}$		1		μs
THD+N	Total harmonic distortion	+ noise	f = 1 kHz, G = 1, V <sub>OUT</sub> = 1 V <sub>RMS</sub>		0.0001%		

<sup>(1) 1000-</sup>hour life test at 125°C demonstrated randomly distributed variation in the range of measurement limits, or approximately 4 µV.

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# Electrical Characteristics: $V_S = \pm 2 \text{ V to } \pm 18 \text{ V (V}_S = 4 \text{ V to } 36 \text{ V)}$ (continued)

At  $T_A = 25$  °C,  $R_L = 10~k\Omega$  connected to  $V_S$  / 2, and  $V_{COM} = V_{OUT} = V_S$  / 2, unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT	г		1		•	
		No load		8	18	mV
	Voltage output swing from rail	$R_L = 10 \text{ k}\Omega$		250	300	mV
		$T_A = -40$ °C to 105°C, $R_L = 10 \text{ k}\Omega$		325	360	mV
I <sub>OS</sub>	Short-circuit current			±18		mA
r <sub>o</sub>	Output resistance (open loop)	f = 2 MHz, I <sub>O</sub> = 0 mA		120		Ω
C <sub>LOAD</sub>	Capacitive load drive			1		nF
POWER	SUPPLY					
Vs	Operating voltage range		±2 (or 4)	±	18 (or 36)	V
	Out			450	525	μA
IQ	Quiescent current (per amplifier)	$T_A = -40$ °C to 105°C, $I_O = 0$ mA			600	μA
TEMPER	RATURE					
	Specified range		-40		105	°C
	Operating range		-40		105	°C

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## 7.8 Typical Characteristics

#### **Table 1. Characteristic Performance Measurements**

DESCRIPTION	FIGURE			
I <sub>B</sub> and I <sub>OS</sub> vs Common-Mode Voltage	Figure 1			
Input Bias Current vs Temperature	Figure 2			
Output Voltage Swing vs Output Current (Maximum Supply)	Figure 3			
CMRR vs Temperature	Figure 4			
0.1-Hz to 10-Hz Noise	Figure 5			
Input Voltage Noise Spectral Density vs Frequency	Figure 6			
Open-Loop Gain and Phase vs Frequency	Figure 7			
Open-Loop Gain vs Temperature	Figure 8			
Open-Loop Output Impedance vs Frequency	Figure 9			
Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)	Figure 10, Figure 11			
No Phase Reversal	Figure 12			
Positive Overload Recovery	Figure 13			
Negative Overload Recovery	Figure 14			
Small-Signal Step Response (100 mV)	Figure 15, Figure 16			
Large-Signal Step Response	Figure 17, Figure 18			
Large-Signal Settling Time (10-V Positive Step)	Figure 19			
Large-Signal Settling Time (10-V Negative Step)	Figure 20			
Short-Circuit Current vs Temperature	Figure 21			
Maximum Output Voltage vs Frequency	Figure 22			
Channel Separation vs Frequency	Figure 23			
EMIRR IN+ vs Frequency	Figure 24			

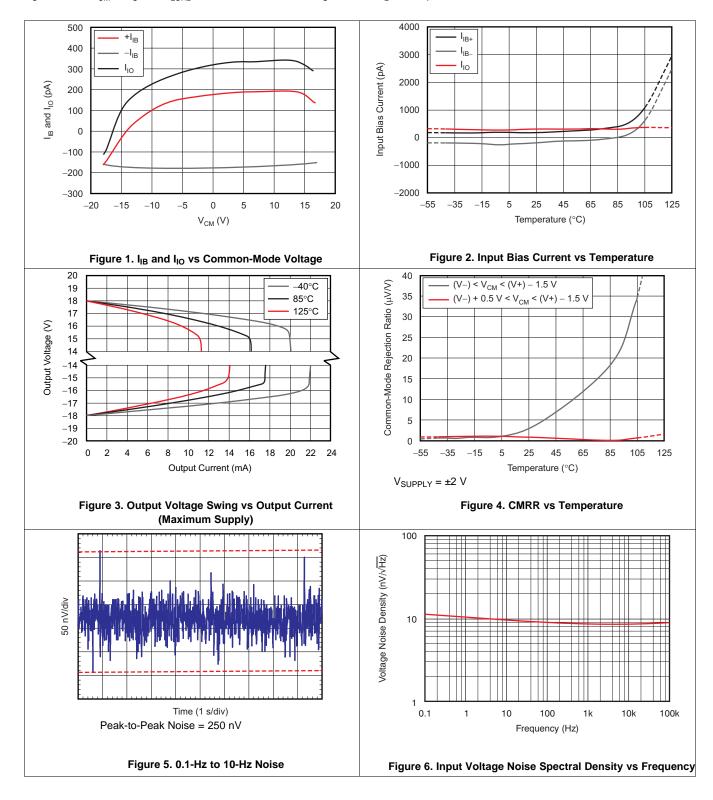
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## 7.9 Typical Characteristics

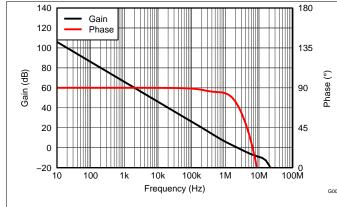
 $V_S$  = ±18 V,  $V_{CM}$  =  $V_S$  / 2,  $R_{LOAD}$  = 10 k $\Omega$  connected to  $V_S$  / 2, and  $C_L$  = 100 pF, unless otherwise noted.



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## **Typical Characteristics (continued)**

 $V_S$  = ±18 V,  $V_{CM}$  =  $V_S$  / 2,  $R_{LOAD}$  = 10 k $\Omega$  connected to  $V_S$  / 2, and  $C_L$  = 100 pF, unless otherwise noted.



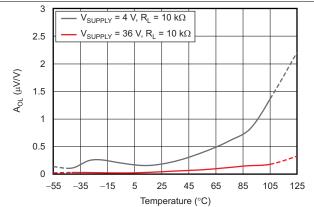
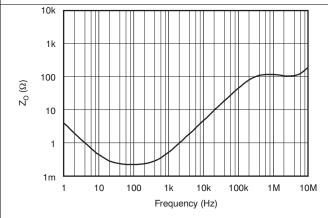


Figure 7. Open-Loop Gain and Phase vs Frequency

Figure 8. Open-Loop Gain vs Temperature



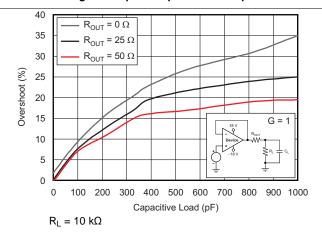
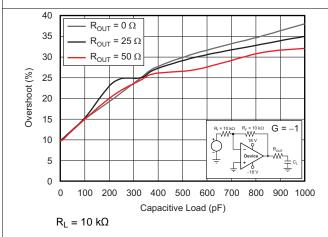


Figure 9. Open-Loop Output Impedance vs Frequency

Figure 10. Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)



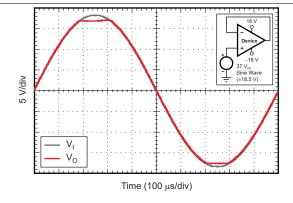


Figure 11. Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)

Figure 12. No Phase Reversal

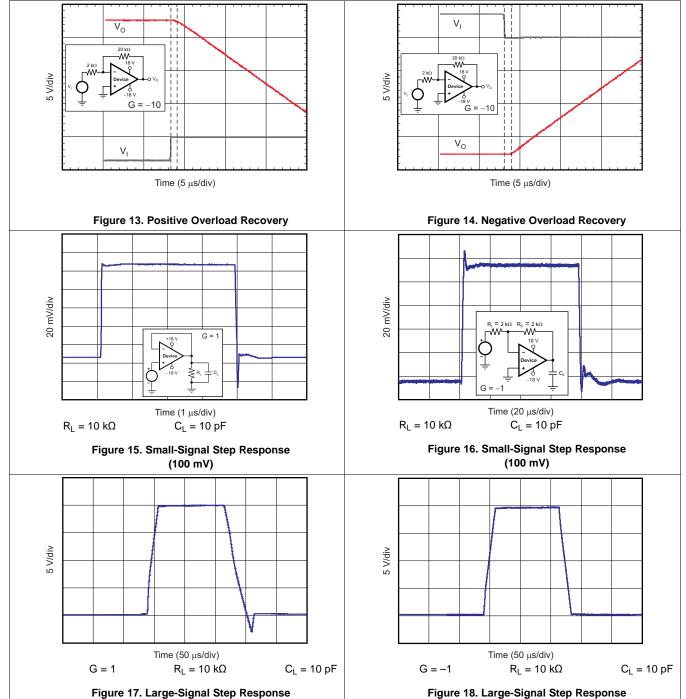
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## **Typical Characteristics (continued)**

 $V_S$  = ±18 V,  $V_{CM}$  =  $V_S$  / 2,  $R_{LOAD}$  = 10 k $\Omega$  connected to  $V_S$  / 2, and  $C_L$  = 100 pF, unless otherwise noted.





## **Typical Characteristics (continued)**

 $V_S = \pm 18$  V,  $V_{CM} = V_S / 2$ ,  $R_{LOAD} = 10$  k $\Omega$  connected to  $V_S / 2$ , and  $C_L = 100$  pF, unless otherwise noted.

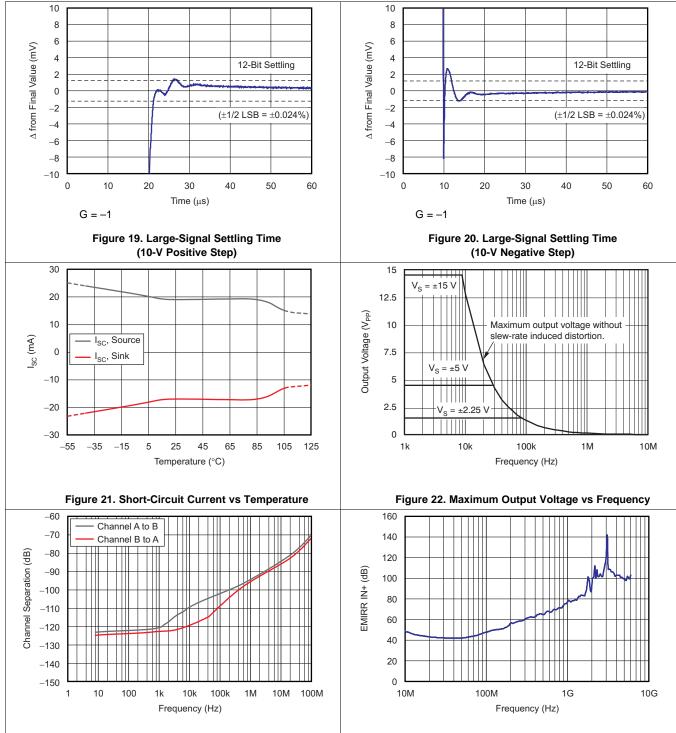


Figure 23. Channel Separation vs Frequency

Figure 24. EMIRR IN+ vs Frequency

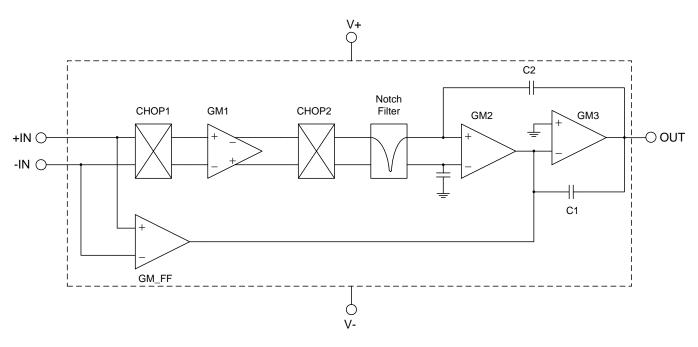


### 8 Detailed Description

#### 8.1 Overview

The OPAx180 family of operational amplifiers combine precision offset and drift with excellent overall performance, making them ideal for many precision applications. The precision offset drift of only 0.1  $\mu$ V/°C provides stability over the entire temperature range. In addition, the devices offer excellent overall performance with high CMRR, PSRR, and A<sub>OL</sub>. As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases, 0.1- $\mu$ F capacitors are adequate.

#### 8.2 Functional Block Diagram



#### 8.3 Feature Description

#### 8.3.1 Operating Characteristics

The OPAx180 family of amplifiers is specified for operation from 4 V to 36 V (±2 V to ±18 V). Many of the specifications apply from -40°C to 105°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the *Typical Characteristics*.

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## **Feature Description (continued)**

#### 8.3.2 EMI Rejection

The OPAx180 uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI interference from sources such as wireless communications and densely populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques; the OPAx180 benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. Figure 25 shows the results of this testing on the OPAx180. Detailed information can also be found in the application report, *EMI Rejection Ratio of Operational Amplifiers* (SBOA128), available for download from www.ti.com.

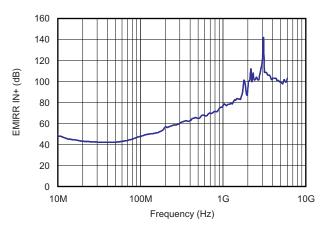


Figure 25. OPAx180 EMIRR Testing

#### 8.3.3 Phase-Reversal Protection

The OPAx180 family has an internal phase-reversal protection. Many op amps exhibit a phase reversal when the input is driven beyond its linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the OPAx180 prevents phase reversal with excessive common-mode voltage. Instead, the output limits into the appropriate rail. This performance is shown in Figure 26.

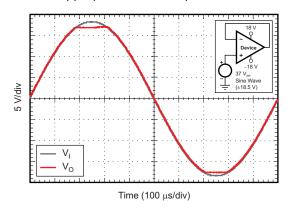


Figure 26. No Phase Reversal

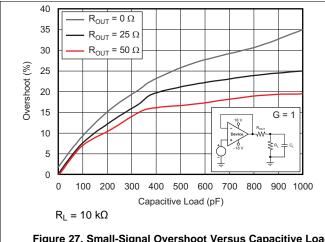
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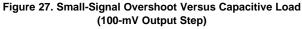


## **Feature Description (continued)**

## 8.3.4 Capacitive Load and Stability

The dynamic characteristics of the OPAx180 have been optimized for a range of common operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (for example,  $R_{OUT}$  equal to 50  $\Omega$ ) in series with the output. Figure 27 and Figure 28 illustrate graphs of small-signal overshoot versus capacitive load for several values of  $R_{OUT}$ . Also, refer to the Applications Report, Feedback Plots Define Op Amp AC Performance (SBOA015), available for download from the TI website, for details of analysis techniques and application circuits.





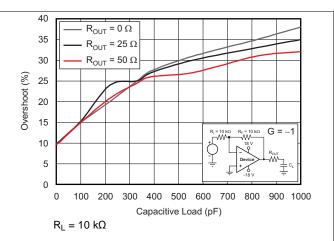


Figure 28. Small-Signal Overshoot Versus Capacitive Load (100-mV Output Step)

#### 8.3.5 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

These ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in the *Absolute Maximum Ratings*. Figure 29 shows how a series input resistor may be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and its value should be kept to a minimum in noise-sensitive applications.

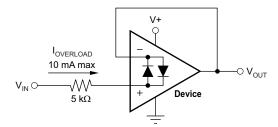


Figure 29. Input Current Protection

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as it discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent it from being damaged. The energy absorbed by the protection circuitry is then dissipated as heat.



#### **Feature Description (continued)**

When the operational amplifier connects into a circuit, the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. Should this condition occur, there is a risk that some of the internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through ESD cells and rarely involves the absorption device.

If there is an uncertainty about the ability of the supply to absorb this current, external zener diodes may be added to the supply pins. The zener voltage must be selected such that the diode does not turn on during normal operation.

However, its zener voltage should be low enough so that the zener diode conducts if the supply pin begins to rise above the safe operating supply voltage level.

#### 8.4 Device Functional Modes

The OPA180, OPA2180, and OPA4180 are powered on when the supply is connected. These devices can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application. In single-supply operation with V— at ground (0 V), V+ can be any value between 4 V and 36 V. In dual-supply operation the supply voltage difference between V— and V+ is from 4 V to 36 V. Typical examples of dual-supply configuration are  $\pm 5$  V,  $\pm 10$  V,  $\pm 15$  V, and  $\pm 18$  V. However the supplies must not be symmetrical. Less common examples are V— at -3V and V+ at 9 V or V— at -16 V and V+ at 5 V. Any combination where the difference between V— and V+ is at least 4 V and no greater than 36 V is within the normal operating capabilities of these devices.

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## 9 Application and Implementation

#### 9.1 Application Information

The OPAx180 family offers excellent dc precision and ac performance. These devices operate up to 36-V supply rails and offer rail-to-rail output, ultra-low offset voltage, and offset voltage drift as well as 2-MHz bandwidth. These features make the OPAx180 a robust, high-performance amplifier for high-voltage industrial applications.

### 9.2 Typical Applications

These application examples highlight only a few of the circuits where the OPAx180 can be used.

#### 9.2.1 Bipolar ±10-V Analog Output from a Unipolar Voltage Output DAC

This design is used for conditioning a unipolar digital-to-analog converter (DAC) into an accurate bipolar signal source using the OPA180 and three resistors. The circuit is designed with reactive load stability in mind and is compensated to drive nearly any conventional capacitive load associated with long cable lengths.

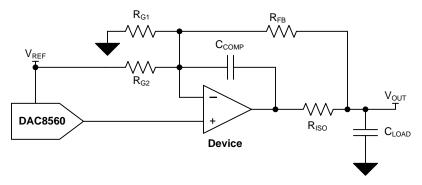


Figure 30. Circuit Schematic

#### 9.2.1.1 Design Requirements

The design requirements are as follows:

• DAC supply voltage: +5-V dc

Amplifier supply voltage: ±15-V dc

Input: 3-wire, 24-bit SPI

Output: ±10-V dc

#### 9.2.1.2 Detailed Design Procedure

#### 9.2.1.2.1 Component Selection

**DAC:** For convenience, devices with an external reference option or devices with accessible internal references are desirable in this application because the reference is used to create an offset. The DAC selection in this design should primarily be based on dc error contributions typically described by offset error, gain error, and integral nonlinearity error. Occasionally, additional specifications are provided that summarize end-point errors of the DAC typically called zero-code and full-scale errors. For ac applications, additional consideration may be placed on slew rate and settling time.

**Amplifier:** Amplifier input offset voltage ( $V_{IO}$ ) is a key consideration for this design.  $V_{IO}$  of an operational amplifier is a typical data sheet specification but in-circuit performance is also affected by drift over temperature, the common-mode rejection ratio (CMRR), and power-supply rejection ratio (PSRR); thus consideration should be given to these parameters as well. For ac operation, additional considerations should be made concerning slew rate and settling time. Input bias current ( $I_{IB}$ ) can also be a factor, but typically the resistor network is implemented with sufficiently small resistor values that the effects of input bias current are negligible.



#### **Typical Applications (continued)**

**Passive:** Resistor matching for the op-amp resistor network is critical for the success of this design and components should be chosen with tight tolerances. For this design 0.1% resistor values are implemented but this constraint may be adjusted based on application-specific design goals. Resistor matching contributes to both offset error and gain error in this design; see the TI Precision Design TIPD125, *Bipolar ±10V Analog Output from a Unipolar Voltage Output DAC* for further details. The tolerance of stability components RISO and CCOMP is not critical and 1% components are acceptable.

#### 9.2.1.3 Application Curves

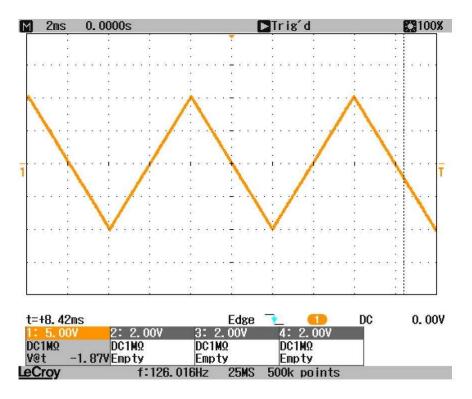


Figure 31. Full-Scale Output Waveform

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## **Typical Applications (continued)**

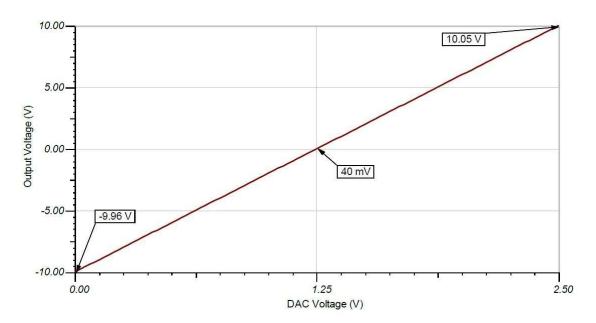


Figure 32. DC Transfer Characteristic



For step-by-step design procedure, circuit schematics, bill of materials, PCB files, simulation results, and test results, refer to TI Precision Design TIPD125, Bipolar ±10V Analog Output from a Unipolar Voltage Output DAC



#### 9.2.2 Discrete INA + Attenuation

The OPA180 can be used as a high-voltage, high-impedance front-end for a precision, discrete instrumentation amplifier with attenuation. The INA159 provides the attenuation that allows this circuit to easily interface with 3.3-V or 5-V analog-to-digital converters (ADCs).

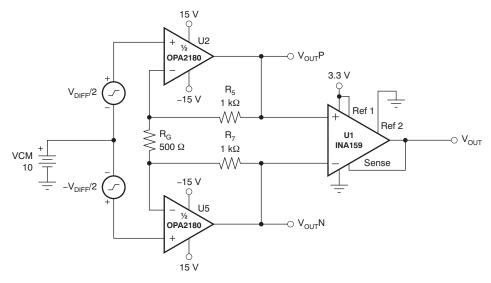
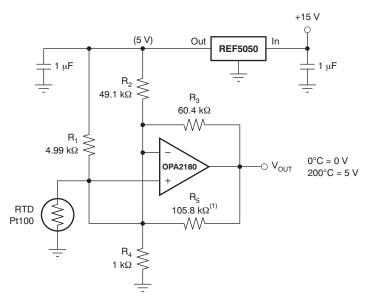


Figure 33. Discrete INA + Attenuation for ADC with 3.3-V Supply

### 9.2.3 RTD Amplifier

The OPA180 is excellent for use in analog linearization of resistance temperature detectors (RTDs). The below circuit combines the precision of the OPA180 amplifier and the precision reference REF5050 to linearize a Pt100 RTD.



(1) R<sub>5</sub> provides positive-varying excitation to linearize output.

Figure 34. RTD Amplifier with Linearization

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## 10 Power Supply Recommendations

The OPA180 is specified for operation from 4 V to 36 V (±2 V to ±18 V); many specifications apply from –40°C to 105°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the *Layout* section.

#### **CAUTION**

Supply voltages larger than 40 V can permanently damage the device; see the *Absolute Maximum Ratings*.

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout* section.

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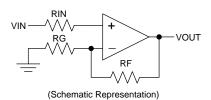
## 11 Layout

#### 11.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
  methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground
  planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically
  separate digital and analog grounds paying attention to the flow of the ground current. For more detailed
  information refer to the Circuit Board Layout Techniques (SLOA089).
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in Figure 35, keeping RF and RG close to the inverting input will minimize parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

#### 11.2 Layout Example



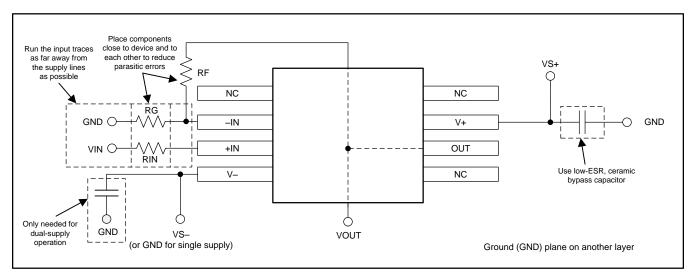


Figure 35. Operational Amplifier Board Layout for Noninverting Configuration

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## 12 Device and Documentation Support

#### 12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 2. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
OPA180	Click here	Click here	Click here	Click here	Click here
OPA2180	Click here	Click here	Click here	Click here	Click here
OPA4180	Click here	Click here	Click here	Click here	Click here

#### 12.2 Trademarks

All trademarks are the property of their respective owners.

## 12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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11-Aug-2014

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
OPA180ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA180	Samples
OPA180IDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	SHJ	Samples
OPA180IDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	SHJ	Samples
OPA180IDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	SHK	Samples
OPA180IDGKT	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	SHK	Samples
OPA180IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA180	Samples
OPA2180ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	2180	Samples
OPA2180IDGK	ACTIVE	VSSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 105	2180	Samples
OPA2180IDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 105	2180	Samples
OPA2180IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	2180	Samples
OPA4180ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA4180	Samples
OPA4180IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA4180	Samples
OPA4180IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA4180	Samples
OPA4180IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 105	OPA4180	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



## PACKAGE OPTION ADDENDUM

11-Aug-2014

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

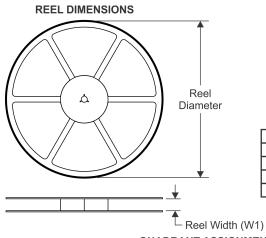
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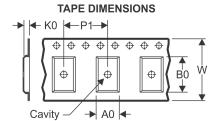
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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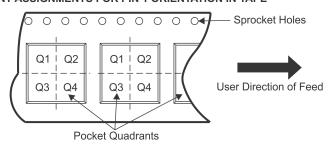
## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

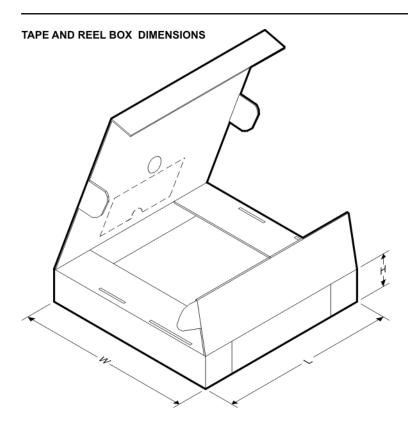
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

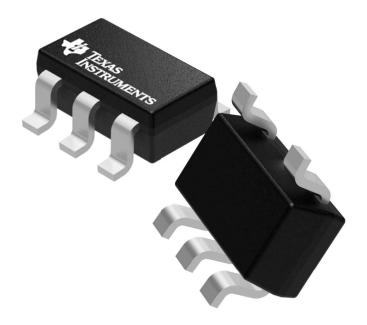
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA180IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA180IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA180IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA180IDGKT	VSSOP	DGK	8	250	177.8	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA180IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2180IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2180IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4180IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
OPA4180IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA180IDBVR	SOT-23	DBV	5	3000	223.0	270.0	35.0
OPA180IDBVT	SOT-23	DBV	5	250	223.0	270.0	35.0
OPA180IDGKR	VSSOP	DGK	8	2500	346.0	346.0	29.0
OPA180IDGKT	VSSOP	DGK	8	250	223.0	270.0	35.0
OPA180IDR	SOIC	D	8	2500	367.0	367.0	35.0
OPA2180IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA2180IDR	SOIC	D	8	2500	367.0	367.0	35.0
OPA4180IDR	SOIC	D	14	2500	367.0	367.0	38.0
OPA4180IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0



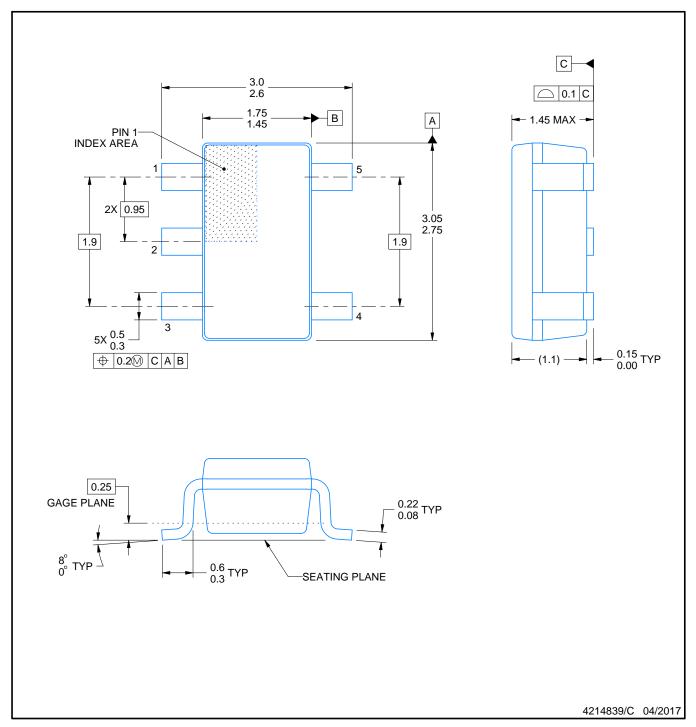
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

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SMALL OUTLINE TRANSISTOR



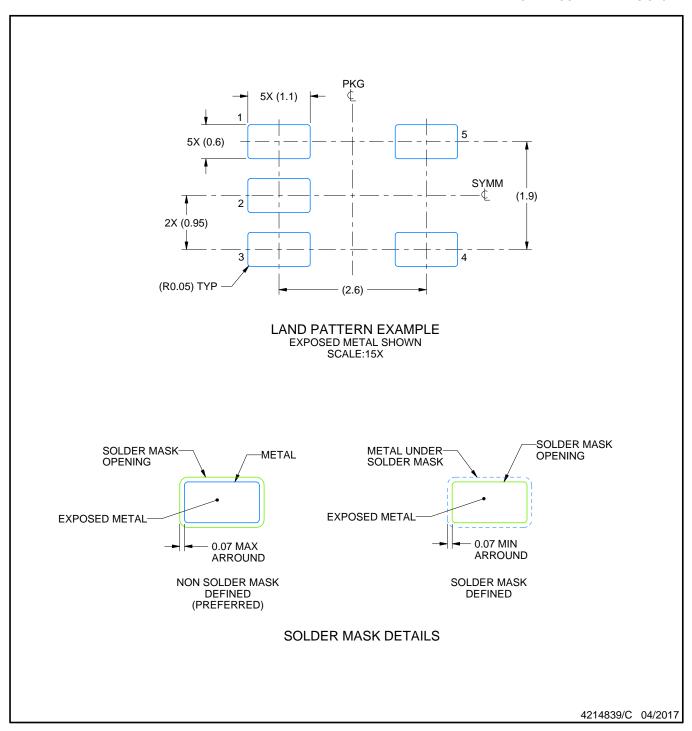
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. Reference JEDEC MO-178.



SMALL OUTLINE TRANSISTOR

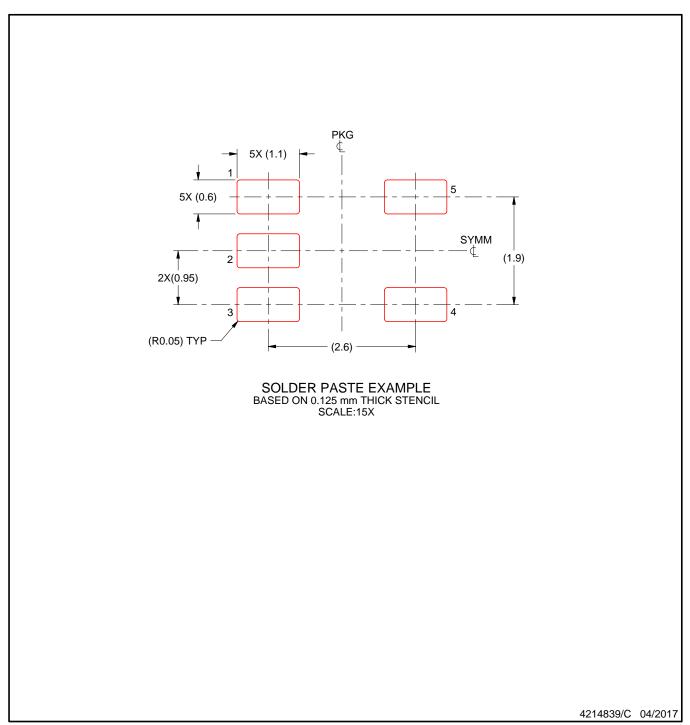


NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



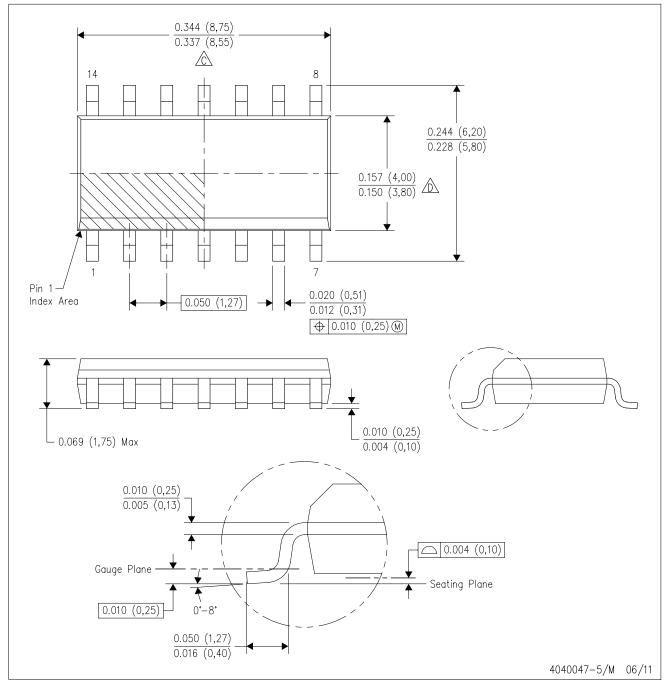
NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.



# D (R-PDSO-G14)

## PLASTIC SMALL OUTLINE

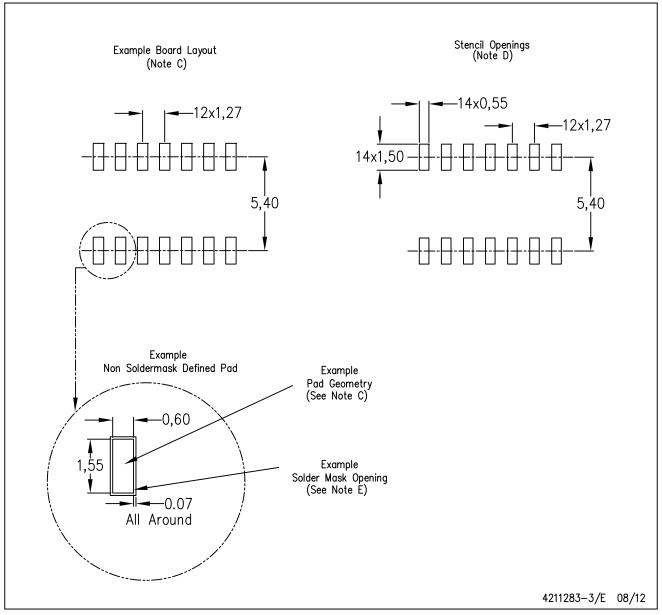


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE

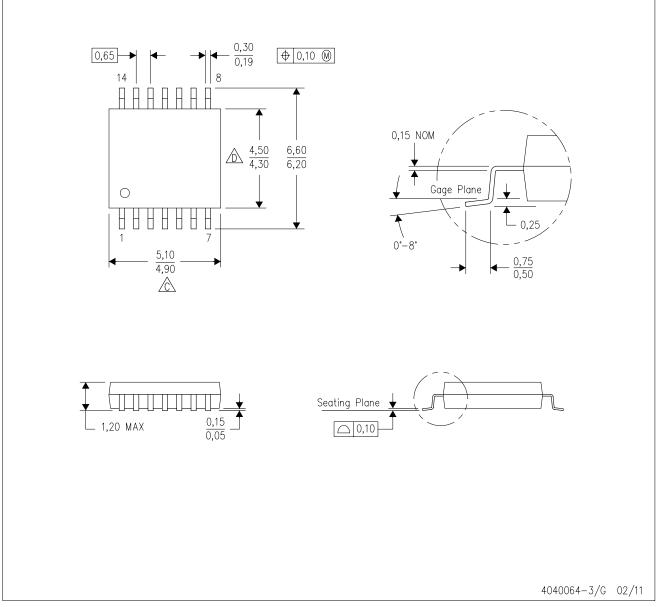


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE

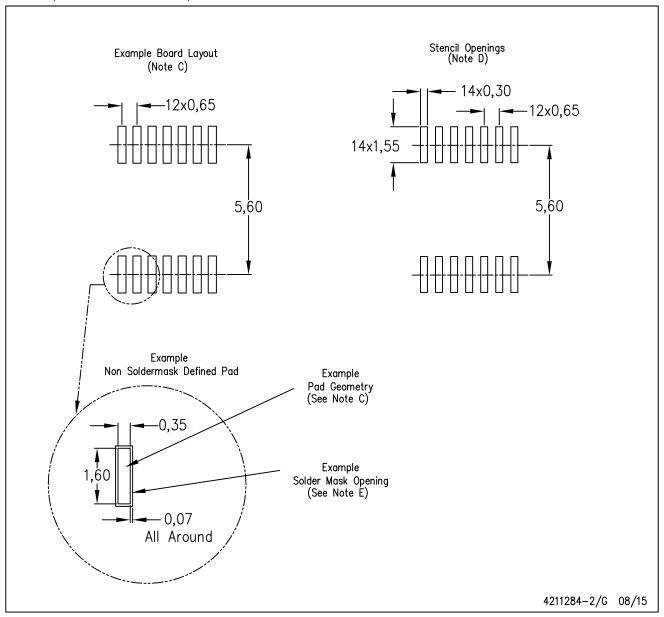


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G14)

# PLASTIC SMALL OUTLINE

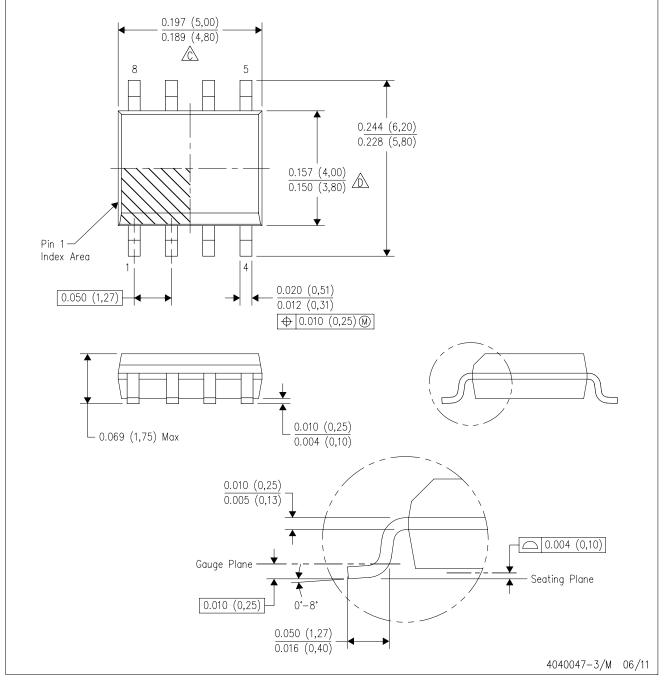


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# D (R-PDSO-G8)

## PLASTIC SMALL OUTLINE

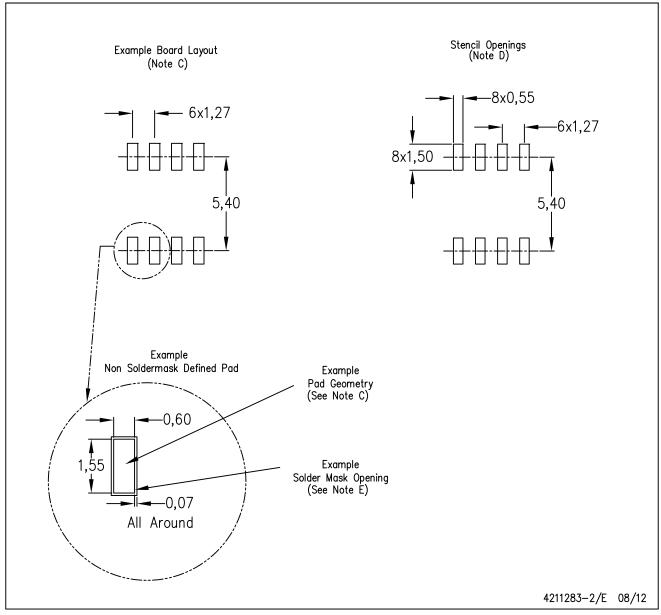


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



# D (R-PDSO-G8)

# PLASTIC SMALL OUTLINE

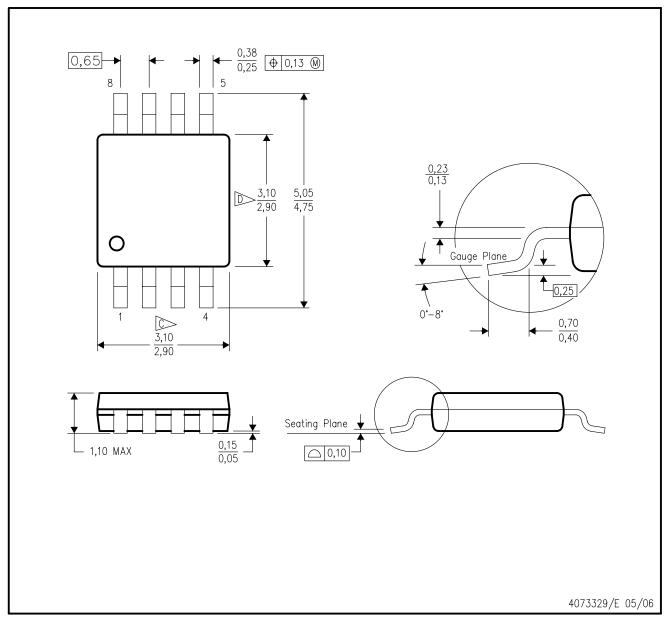


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# DGK (S-PDSO-G8)

# PLASTIC SMALL-OUTLINE PACKAGE

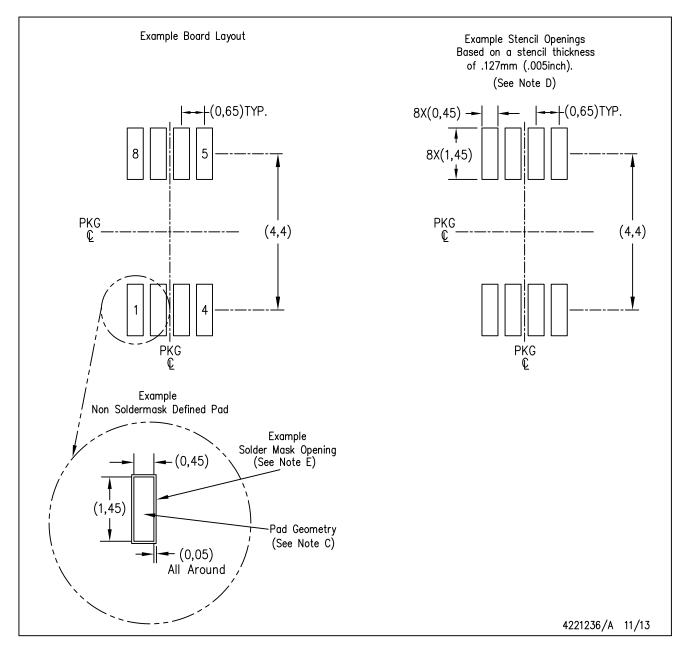


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



# DGK (S-PDSO-G8)

## PLASTIC SMALL OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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